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(71) Applicants *(for all designated States except US)*: **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, CA 94538 (US). **LI, Lumin** [US/US]; 3480 Tracy Drive, Santa Clara, CA 95051 (US). **SADJADI, Reza** [US/US]; 19413 Vineyard Lane, Saratoga, CA 95070 (US).

(72) Inventor; and

(75) Inventor/Applicant *(for US only)*: **HUANG, Zhisong** [US/US]; 5972 Roxie Terrace, Fremont, CA 94555 (US).

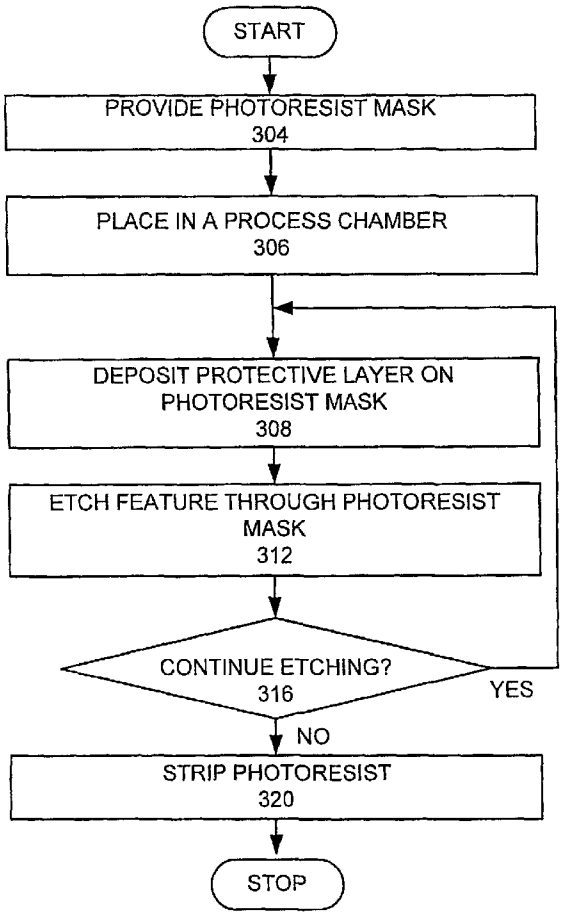
(74) Agent: **OLYNICK, Mary, R.**; Beyer Weaver & Thomas, LLP, P.O. Box 778, Berkeley, CA 94704-0778 (US).

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(54) Title: A METHOD FOR PLASMA ETCHING PERFORMANCE ENHANCEMENT



(57) Abstract: A method for etching a feature in a layer through an etching mask is provided. A protective layer is formed on exposed surfaces of the etching mask and vertical sidewalls of the feature with a passivation gas mixture. The feature is etched through the etching mask with reactive etching mixtures containing at least one etching chemical and at least one passivation chemical.

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